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Large effective mass and interaction-enhanced Zeeman splitting of K-valley electrons in $MoSe_2$

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We study the magnetotransport of high-mobility electrons in monolayer and bilayer $MoSe_2$, which show Shubnikov–de Haas (SdH) oscillations and quantum Hall states in high magnetic fields. An electron effective mass of $0.8m_e$ is extracted from the SdH oscillations' temperature dependence; m_e is the bare electron mass. At a fixed electron density the longitudinal resistance shows minima at filling factors (FFs) that are either predominantly odd, or predominantly even, with a parity that changes as the density is tuned. The SdH oscillations are insensitive to an in-plane magnetic field, consistent with an out-of-plane spin orientation of electrons at the K point. We attribute the FF parity transitions to an interaction enhancement of the Zeeman energy as the density is reduced, resulting in an increased Zeeman-to-cyclotron energy ratio.

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Group VI transition-metal dichalcogenides (TMDs) 1H-monolayers are direct bandgap two-dimensional (2D) semiconductors with band extrema at the corners (K point) of the hexagonal Brillouin zone [1]. The combination of strong spin-orbit interaction (SOI) and broken inversion symmetry results in a large bandgap at the K point, and a spin-split bandstructure with coupled spin and valley degrees of freedom [2–4]. Magnetotransport in clean TMD samples can be used to probe the energy-momentum dependence at the band extrema, the Landau level (LL) structure, and assess the impact of electron-electron interaction via negative compressibility or enhanced Zeeman splitting. Shubnikov–de Haas (SdH) oscillations of K-valley holes in mono- and bilayer WSe_2 have revealed predominantly twofold degenerate LLs [5], and interaction-enhanced Zeeman splitting [6,7]. Similarly, Γ-valley holes in few-layer WSe_2 show large effective masses and enhanced Zeeman splitting [8]. Magnetotransport of 2D electrons in TMDs has been hindered by challenges in obtaining high-mobility samples and low-temperature Ohmic contacts [9]. Magnetotransport in few-layer MoS_2 and WS_2 samples reveal three- or sixfold degenerate LLs, consistent with Q-valley conduction band (CB) extrema [10–12]. Compressibility studies of monolayer WSe_2 reveal comparable K-valley electron and hole effective masses, and interaction-enhanced LL Zeeman splitting in the valence band (VB), but not in the CB [7].

Here, we report a study of SdH oscillations in high-mobility electrons in dual-gated mono- and bilayer $MoSe_2$, using Pd bottom contacts. From the temperature dependence of the SdH oscillation amplitude, we extract an electron effective mass of $0.8m_e$; m_e is the bare electron mass. We observe predominantly even or odd filling factors (FFs) depending on the electron density (n), an observation explained by an interaction-enhanced Zeeman splitting with reducing density. Tilted magnetic-field measurements indicate that the electron spin is locked perpendicular to the $MoSe_2$ plane.

Our devices are fabricated using $MoSe_2$ flakes exfoliated from synthetic crystals (HQ Graphene). Mono- and bilayer flakes are identified using a combination of Raman and photoluminescence (PL) spectroscopy. Figure 1(a) shows the normalized PL spectra for both mono- and bilayer flakes, at room temperature, using an excitation wavelength of 532 nm. The monolayer (bilayer) PL spectrum features a single prominent peak at 1.57 (1.53) eV, associated with the A exciton [13,14]. Figure 1(b) shows a cross-section schematic of a dual-gated, hexagonal boron nitride (hBN)-encapsulated $MoSe_2$ device with bottom Pd contacts, fabricated using a layer pickup and transfer method [15,16]. Figure 1(c) shows an optical micrograph of a device with top and bottom graphite gates. Devices with metal gates show similar results. The Pd bottom contacts along with $MoSe_2$ electrostatic doping at positive top-gate bias (V_{TG}) provide n-type Ohmic contacts at low-temperatures. Data from two monolayer (A1, A2), and three bilayer (B1, B2, B3) $MoSe_2$ samples are included in this study. The measurements were carried out at temperatures down to $T = 0.3$ K, and magnetic fields up to 35 T.

Figure 1(d) shows the longitudinal (R_{xx}) and Hall (R_{xy}) resistance as a function of the perpendicular magnetic field (B) measured in bilayer $MoSe_2$ sample B1 at $n = 4.9 \times 10^{12}$ cm^{-2}, and $T = 0.3$ K. The data show SdH oscillations developing at $B > 6$ T, corresponding to a mobility $\mu \simeq 1650$ cm^2/V s. At high B fields, quantum Hall states (QHSs) develop at $\nu = 6, 8, 10$; $\nu = nh/eB$, where e is the electron charge, and h is Planck's constant. Similar data measured in monolayer $MoSe_2$ sample A1 are included in the Supplemental Material [17].

Figures 2(a) and 2(b) show R_{xx} vs B measured at different bottom-gate biases (V_{BG}) in monolayer A1 at $V_{TG} = 8$ V, $T = 0.3$ K, and in bilayer B2 at $V_{TG} = 6.5$ V, $T = 1.5$ K, respectively. Figures 2(c) and 2(e) show the Fourier transform

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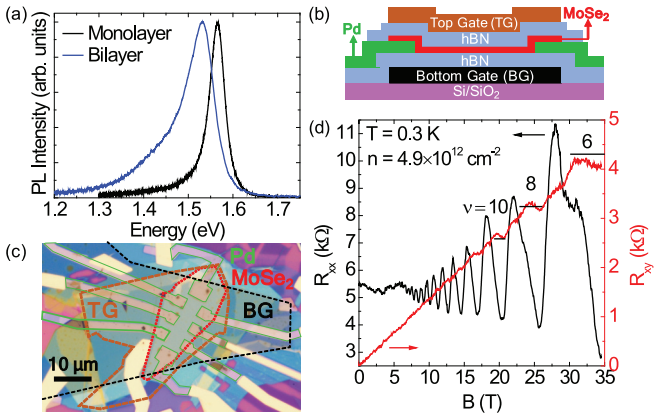

FIG. 1. (a) Normalized room-temperature PL spectra of mono- and bilayer $MoSe_2$. (b) Schematic cross section and (c) optical micrograph of a dual-gated, hBN-encapsulated $MoSe_2$ device. Outlines of different colors mark the $MoSe_2$ flake (red), Pd contacts (green), top (orange) and bottom (black) graphite gates. (d) R_{xx} (left axis) and R_{xy} (right axis) vs B measured at $T = 0.3$ K and $n = 4.9 \times 10^{12}$ cm^{-2} in bilayer $MoSe_2$ B1.

(FT) amplitude vs frequency corresponding to R_{xx} vs B^{-1} data of Figs. 2(a) and 2(b), respectively. The FT is performed by first subtracting a polynomial background from the R_{xx} vs B^{-1} data to center it around zero, followed by a Hamming window multiplication, and a fast FT algorithm.

Figure 2(c) data, corresponding to monolayer $MoSe_2$, reveal one principal peak at a frequency (f) for $V_{BG} \leqslant 0$ V. For $V_{BG} > 0$ V, f shows a weaker V_{BG} dependence, and a second, lower-frequency peak (f') emerges, indicating a second subband is populated. The subband, $(2e/h)f$ and $(2e/h)f'$, and the total $(2e/h)(f + f')$ densities, along with the n values determined from the R_{xy} slope at low B fields are summarized as a function of V_{BG} in Fig. 2(d). The electron density determined from the SdH oscillation frequency is obtained assuming twofold degenerate LLs. The total n displays a linear dependence on V_{BG}. At $n > 12.5 \times 10^{12}$ cm^{-2} the second subband (f') is populated, as marked in Fig. 2(d). The SOI leads to a splitting of the spin-up and spin-down states at the K point in TMDs. This splitting is ≈0.2 eV and ≈25 meV for monolayer $MoSe_2$ VB [1] and CB [4,18,19], respectively. We associate the peaks f and f' in Figs. 2(c) and 2(d) with the population of the lower and upper CB spin-split bands of monolayer $MoSe_2$, respectively.

Figure 2(e) data, corresponding to bilayer $MoSe_2$, reveal one principal peak at a frequency f, and its second harmonic ($2f$) indicating a single subband is occupied. The f value increases linearly with V_{BG}, consistent with Fig. 2(c) data in monolayer $MoSe_2$ with only the lowest spin-split subband populated. Figure 2(f) shows a comparison between $n = (2e/h)f$ calculated using the f values of Fig. 2(e), and the n values determined from the R_{xy} slope at low B fields as a function of V_{BG}.

Figure 3(a) shows R_{xx} vs B data measured at various T values, at constant $n = 4.9 \times 10^{12}$ cm^{-2} in bilayer B1. Using the temperature (T) dependence of the SdH oscillation amplitude (ΔR_{xx}) we extract the electron effective mass (m^*) as $\Delta R_{xx} \propto \xi/\sinh\xi$, where $\xi = 2\pi^2 k_B T/\hbar\omega_c$ and $\omega_c = eB/m^*$; k_B is the

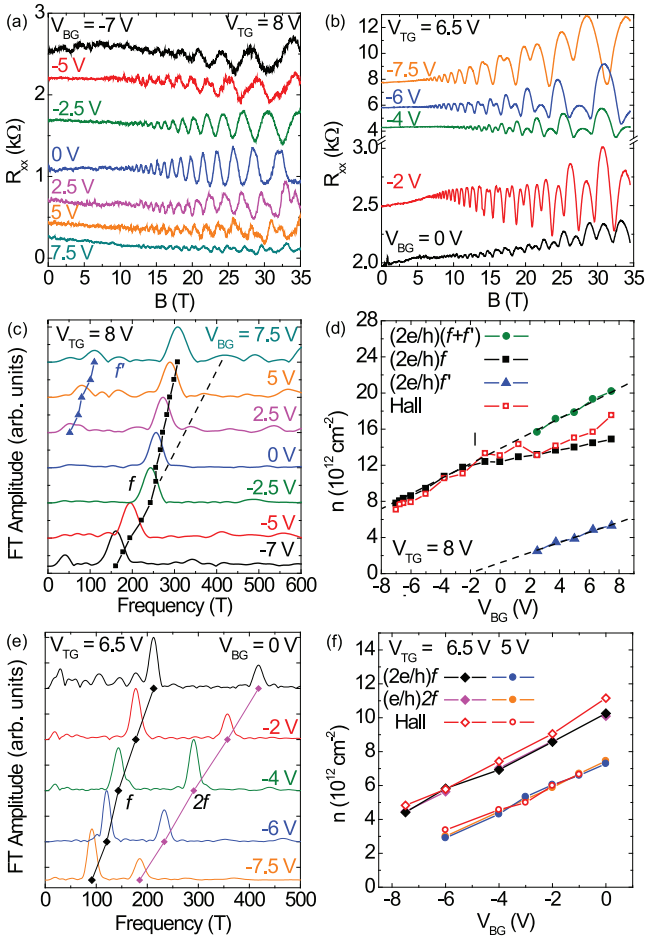

FIG. 2. (a) R_{xx} vs B measured at various V_{BG} values, $V_{TG} = 8$ V, and $T = 0.3$ K in monolayer $MoSe_2$ A1. (b) R_{xx} vs B measured at various V_{BG} values, $V_{TG} = 6.5$ V, and $T = 1.5$ K in bilayer $MoSe_2$ B2. The traces in (a) and (b) are offset for clarity. (c), (e) Normalized FT amplitude vs frequency corresponding to R_{xx} vs B^{-1} data of (a) and (b), respectively. (d) n vs V_{BG} measured in monolayer $MoSe_2$ A1 at $V_{TG} = 8$ V. The onset of the upper spin-split subband population is marked. (f) n vs V_{BG} measured in bilayer $MoSe_2$ B2 at $V_{TG} = 6.5$ V (diamonds) and $V_{TG} = 5$ V (circles). Solid (open) symbols correspond to n determined from FT (R_{xy}) data.

Boltzmann constant, and $\hbar$ is the reduced Planck's constant [17]. Figure 3(b) shows m^*/m_e vs B data for monolayer A1, and bilayer B1, B2 at n ranging between 4.9×10^{12} and 12.4×10^{12} cm^{-2}, where only the lower spin-split CB at the K point is probed. The average $m^*/m_e = 0.8$ is largely insensitive to n and B. Theoretical calculations of m^*/m_e in monolayer $MoSe_2$ range between 0.50 and 0.56 [4,19,20]. The measured m^* values, and the corresponding density of states ($m^*/\pi\hbar^2$) allow us to determine the CB spin splitting ($2\Delta_{cb}$) in monolayer $MoSe_2$. Considering the threshold density for the population of the upper CB subband $n_T = 12.5 \times 10^{12}$ cm^{-2} [Fig. 2(d)], we obtain $2\Delta_{cb} = n_T \pi\hbar^2/m^* = 37$ meV, a value comparable to, albeit larger than theoretical calculations [4,18,19].

The CB minima are expected to be at the K point in monolayer, and at the Q point in bulk $MoSe_2$ [21,22]. The data of Figs. 1–3 allow us to unambiguously determine the CB minima in mono- and bilayer $MoSe_2$. The twofold LL degeneracy

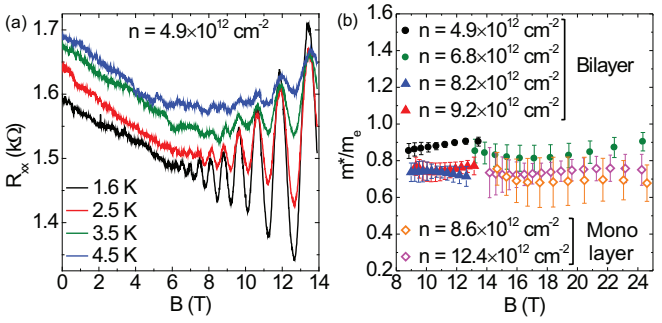

FIG. 3. (a) R_{xx} vs B measured at various T values, at $n = 4.9 \times 10^{12}$ cm^{-2} in bilayer $MoSe_2$ B1. (b) m^*/m_e vs B measured at different n in monolayer $MoSe_2$ A1 (◇), bilayer $MoSe_2$ B1 (●), and B2 (▲).

observed in both mono- and bilayer samples is consistent with CB minima at the K point, as SdH oscillations of carriers at the Q point show three- or sixfold degenerate LLs [10,11]. The similar m^* values of Fig. 3(b) for mono- and bilayer $MoSe_2$ further support this conclusion. In group VI TMD bilayers, the weak interlayer coupling of K-valley carriers leads to two distinct subbands for each layer [5], with densities that can be independently controlled by V_{TG} and V_{BG}. For $V_{TG} > 0$ V and $V_{BG} \leqslant 0$ V only the top layer is populated, and the bilayer $MoSe_2$ can be effectively treated as a monolayer. The absence of a beating pattern in bilayer SdH oscillations up to $n = 11.0 \times 10^{12}$ cm^{-2} [Fig. 2(b)] indicates the electrons populate the lower spin-split subband of the top layer.

Figure 4(a) shows R_{xx} vs ν at different n values between 2.9×10^{12} and 11.0×10^{12} cm^{-2} measured in bilayer B2. For n values larger than 8.6×10^{12} cm^{-2}, R_{xx} minima are present at predominantly odd FFs. At $n = 7.0 \times 10^{12}$ cm^{-2}, the R_{xx} minima at odd and even FFs are of equal strength up to $\nu = 36$. As n is lowered to 5.6×10^{12} cm^{-2}, the FF sequence turns predominantly even, and at $n = 4.5 \times 10^{12}$ cm^{-2} the odd FF R_{xx} minima are absent. At the lowest $n = 2.9 \times 10^{12}$ cm^{-2} another transition to odd FFs is observed. We note that at fixed n the FF sequence is insensitive to changes in the transverse electric field [17].

To better understand the n-dependent FF sequence, we write the LL CB energies $E_{l,\tau s} = \tau s \Delta_{cb} + (l + 1/2)E_c + s g_s \mu_B B/2 + \tau g_v \mu_B B/2$, where $l = 0,1,2,\ldots$ is the LL orbital index, $s = \pm 1$ corresponds to the electron spin $\uparrow$ and $\downarrow$, $\tau = \pm 1$ to the K and K' valleys, $E_c = \hbar\omega_c$ is the cyclotron energy, μ_B is the Bohr magneton, and g_v, g_s are the valley and spin g-factors, respectively. The $\tau s \Delta_{cb}$ term describes the spin-split CB minima where the LLs originate. The $\tau s = \pm 1$ doublets lead to two LL fan diagrams with an energy separation of $2\Delta_{cb}$ at $B = 0$. We assume that electrons reside in the lowest spin-split band ($\tau s = -1$), where the total, spin, and valley LL Zeeman energy is $E_Z|_{\tau s=-1} = \tau g^* \mu_B B$; $g^* = g_v - g_s$ is the effective g-factor for LLs of the lowest CB spin-split subband. The LL energies of the $\tau s = -1$ group write $E_{l,\tau} = (l + 1/2)E_c + \tau g^* \mu_B B/2$. We use here the single-band model convention in which all LLs are twofold degenerate in the absence of Zeeman splitting [4,23]. Using a model in which the $l = 0$ is nondegenerate [3] is equivalent to a g^* offset by $2m_e/m^*$.

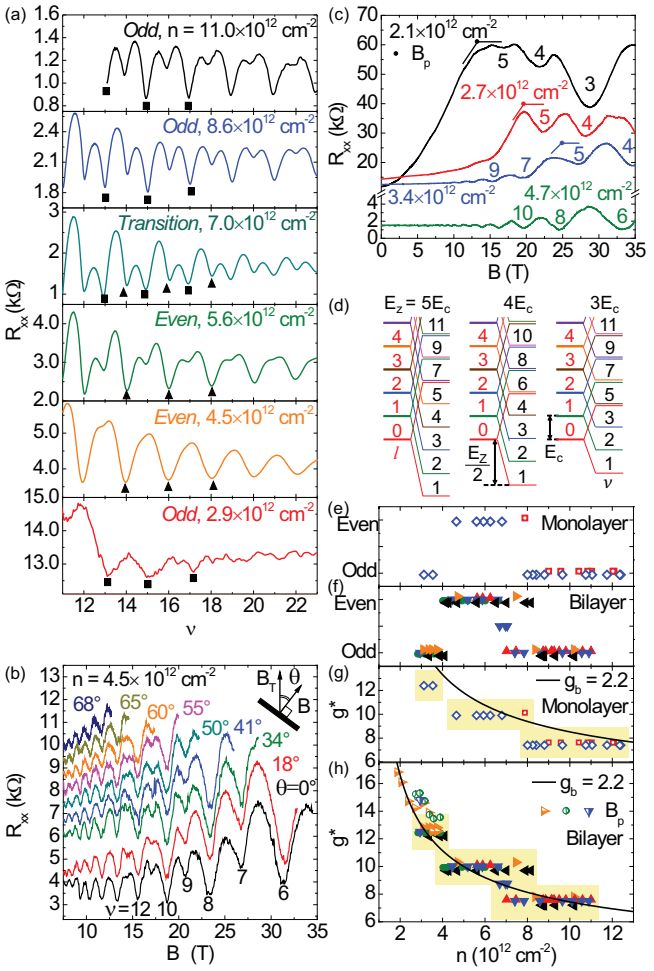

FIG. 4. (a) R_{xx} vs ν measured at n values between 2.9×10^{12} and 11.0×10^{12} cm^{-2}, $T = 1.5$ K in bilayer $MoSe_2$ B2. The FF sequence undergoes parity transitions at $n = 7.0 \times 10^{12}$ cm^{-2}, and $n = 4.0 \times 10^{12}$ cm^{-2}. The triangles (squares) mark R_{xx} minima at even (odd) FFs. (b) R_{xx} vs B measured at different θ, at $n = 4.5 \times 10^{12}$ cm^{-2}, and $T = 1.5$ K in bilayer B2. The traces are offset for clarity. Inset: Sample orientation schematic. (c) R_{xx} vs B measured at n between 2.1×10^{12} and 4.7×10^{12} cm^{-2}, $T = 0.3$ K in bilayer B3. (d) LL structure highlighting the interplay between E_Z and E_c. An even (odd) E_Z/E_c corresponds to an even (odd) FF sequence. (e), (f) FF parity vs n in mono- and bilayer $MoSe_2$, respectively. Symbol legend: Monolayer A1 (◇), A2 (○); bilayer B1 (●), B2 (▲,▼), B3 (◀, ▶); ▲,▼ and ◀, ▶ label different cooldowns. (g), (h) g^* vs n in mono- and bilayer $MoSe_2$, respectively, and fit to the QMC calculations using $g_b = 2.2$ (solid line). The shaded region indicates the g^* error bar $\Delta g^* = \pm m_e/m^*$.

The Zeeman-to-cyclotron energy ratio determines the FF sequence, with even (odd) E_Z/E_c values leading to even (odd) FFs. Figure 4(a) data reveal a B-field independent FF sequence at a fixed n, indicating that E_Z/E_c does not vary with the B field. The FF parity transitions can be explained by an n-dependent E_Z/E_c, or equivalently by an n-dependent, interaction-enhanced g^*. Consistent with the large effective mass, electron-electron interaction is expected to enhance g^* as n is reduced, as reported in Si [24,25], GaAs [26], AlAs [27], and WSe_2 [6–8] 2D systems.

Magnetotransport in magnetic fields tilted at an angle (θ) from the 2D plane normal [Fig. 4(b) inset] has been employed to probe the Zeeman splitting in 2D systems. If E_Z is proportional to the total magnetic field (B_T), the FF sequence changes with θ [24]. Figure 4(b) shows R_{xx} vs B at various θ values and $n = 4.5 \times 10^{12}$ cm^{-2} in bilayer B2. At $\theta = 0^\circ$ the FF sequence is predominantly even, and remains unchanged for all θ values, indicating that E_Z is insensitive to the parallel magnetic field component. These findings contrast observations in Si [24,25], GaAs [26], AlAs [27], and few-layer WSe_2 [8] 2D systems, but are in agreement with observations in trilayer MoS_2 [11], and mono- and bilayer WSe_2 [6], where the combination of strong SOI and band extrema away from the Brillouin zone center locks the carrier spin perpendicular to the 2D system.

Figure 4(c) shows examples of R_{xx} vs B measured in bilayer B3 at low n values. For $n < 4.0 \times 10^{12}$ cm^{-2} the data show QHSs at consecutive FFs above a density-dependent field (B_p), where the occupied LLs have the same spin orientation. Interestingly, the observation of consecutive FFs above B_p is accompanied by a pronounced positive magnetoresistance (MR) background superimposed onto the SdH oscillations for $B < B_p$, similar to the positive MR associated with a parallel magnetic-field-induced spin polarization in Si, GaAs, and AlAs 2D systems [25,27,28].

A quantitative determination of g^* is possible using FF sequence parity data [Fig. 4(a)], and the spin-polarization field [Fig. 4(c)]. Figure 4(d) illustrates the LL structure, where the E_c and E_Z contributions are shown separately for different E_Z/E_c values and FF sequences. Figures 4(e) and 4(f) summarize the FF sequence parity vs n measured in mono- and bilayer samples, respectively. Comparing the diagram in Fig. 4(d) and the FF sequence ($\nu = 4,5,7,9,11,\ldots$), associated with R_{xx} vs B data measured at $n = 3.4 \times 10^{12}$ cm^{-2} in bilayer B3 [Fig. 4(c)] allows to assign $E_Z/E_c = 5$ to the lowest n FF parity group of Fig. 4(f). The observation of consecutive integer FFs above a certain magnetic field [Fig. 4(c)] allows us to unambiguously assign E_Z/E_c. As n is increased, each FF sequence transition is associated with a decrease in E_Z equal to E_c [Figs. 4(e) and 4(f)], consistent with a decreasing g^* as the 2D system becomes less dilute. A FF sequence associated with a transition is assigned to a half-integer E_Z/E_c value. Once we assign an $i = E_Z/E_c$ value to each FF sequence group [Figs. 4(e) and 4(f)], namely, $i = 5,4,3$, we determine $g^* = (2m_e/m^*)i$ as a function of n as shown in Figs. 4(g) and 4(h) for both mono- and bilayer samples, respectively. At the onset of full spin polarization E_Z is equal to the Fermi energy, and $B_p = 2hn/(eg^*m^*/m_e)$ [28]. At low n values the B_p vs n measurement provides a separate method to determine g^* vs n. The g^* values obtained from B_p values and FF sequence transitions are summarized in Fig. 4(h) for bilayer samples.

Quantum Monte Carlo (QMC) spin susceptibility calculations [29] have shown good agreement with experiments in GaAs [26] and AlAs [27] 2D electrons, and in WSe_2 2D holes in the K valley [6]. A comparison between the measured g^* and QMC results requires the band g-factor value (g_b) in the absence of interaction effects. As the g_b value remains to be established for $MoSe_2$ [4,23,30], we estimate $g_b = 2.2$ using a fit of the QMC spin susceptibility [29] to the experimental g^* vs n data for both mono- [Fig. 4(g)] and bilayer [Fig. 4(h)] samples assuming implicitly the QMC calculations approximate well the interaction enhancement of g^* in $MoSe_2$ as in other 2D systems [6,26,27]. The n value is converted into a dimensionless interparticle distance $r_s = 1/(\sqrt{\pi n}a_B^*)$, where $a_B^* = a_B(\kappa m_e/m^*)$ is the effective Bohr radius, and κ the effective dielectric constant [31]; a_B is the Bohr radius.

In summary, we report magnetotransport studies in high-mobility mono- and bilayer $MoSe_2$. The SdH oscillations reveal a density-dependent FF sequence, and a K-valley electron effective mass of $0.8m_e$. The FF sequence is insensitive to a parallel magnetic field, indicating the electron's spin is locked perpendicular to the $MoSe_2$ plane. The interplay between cyclotron and Zeeman energy, along with an interaction-enhanced, density-dependent g-factor explains the FF sequence odd-to-even transitions. These findings clarify the LL structure of K-valley electrons in $MoSe_2$, and highlight the role of interactions in this large effective mass 2D system.

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[31] The κ value for a 2D system at the interface between two dielectrics is $\kappa(t,b) = [(\epsilon_t^{\parallel}\epsilon_t^{\perp})^{1/2} + (\epsilon_b^{\parallel}\epsilon_b^{\perp})^{1/2}]/2$, where $\epsilon_{t(b)}^{\parallel/\perp}$ is the the top (bottom) relative dielectric constant with respect to the 2D plane normal. For monolayer $MoSe_2$, $\kappa = \kappa(\text{hBN,hBN})$, where $\epsilon_{\text{hBN}}^{\parallel} = 3.0$, $\epsilon_{\text{hBN}}^{\perp} = 6.9$, [32]. For bilayer $MoSe_2$, the dielectric environment of electrons in the top layer is altered by the depleted $MoSe_2$ bottom layer, for which the following average is used, $\kappa = [\kappa(\text{hBN,hBN}) + \kappa(\text{hBN,MoSe}_2)]/2$, where $\epsilon_{\text{MoSe}_2}^{\perp} = 15.5$ [33], $\epsilon_{\text{MoSe}_2}^{\parallel} = 4$ [34].
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